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The *Patterson function* has been the most useful and generally applicable approach to the solution of the phase problem, and over the years a number of ingenious methods of unraveling the Patterson function have been proposed. Many of these methods involve multiple superpositions of parts of the map, or "image-seeking" with known vectors. Such processes are ideally suited to machine computation. Whereas the great increase in the power of x-ray methods of structure determination in the past few years has come simply from our ability to compute a three-dimensional Patterson function, it is reasonable to expect that as machine methods of unraveling the Patterson function are developed, this power will increase many fold.

Step (3), the refinement of crystal structure, continues to enjoy a considerable amount of interest. Reasonably complete refinement is routine these days, owing in large measure to the availability of suitable computers. For reasons that are both practical and mathematically sound, the least-squares approach to refinement has gained favor over the successive structure-factor-Fourier approach. Yet the computational problems often tax this generation of computers. If one assigns a single isotropic thermal parameter to each atom, then there are four parameters, three positional and one thermal, to be determined for each atom. In the least-squares procedure, if one stores the upper right triangle of the normal-equations' matrix, then $\frac{1}{2}N(N+1)$ elements are required, where N is the number of variables. In a machine with a memory of 32,000 words, a practical limit is reached at about $N = 200$, if one wishes to keep the rest of the program in core. Thus refinement of a 50-atom problem often taxes the memory capacity of the machine, and for larger problems special computational or mathematical tricks are needed. One of these tricks is to make use of known features of the structure or the thermal motion to reduce the number of parameters. But, even with increased numbers and more rapid availability of data, computerized solutions to crystallographic problems still suffer from a degree of uniqueness. Programs written to operate on one machine must often be extensively revised to be used on another. An international group of workers at the National Resource for Computation in Chemistry at the Lawrence Berkeley Laboratory is trying to overcome this problem of interchangeability by writing a program designed to run on any medium or large sized computer. When completed, the program will allow a crystallographer, armed only with experimental data and a computer, to determine the structure of any crystal without having to write special programs.

Crystal Growth. The direct growth of an ideal and perfect crystal is difficult except at very high supersaturations because of the difficulty of nucleating a new surface on a completed surface of the crystal. But, if there is a screw dislocation present, it is not necessary to start a new surface, and growth proceeds in a spiral fashion by the accretion of atoms at the edge of growth steps. The resultant growth spirals have been observed, and it is believed that most crystals grow in this manner. See Fig. 5. But spiral growth is not the only mechanism which enables crystal growth at fast rates. Gilmer, in particular, has employed computer simulation models in studies of crystal growth and has demonstrated that, among other influences, temperature and impurity levels have decisive effects upon growth rates. Again, since different crystal faces have different kinetic properties, the particular crystal plane exposed to growth will also be a partial

determinant of growth rate.

In modern technology based upon solid state chemistry and physics, much emphasis is placed upon the availability of elements and compounds in single-crystal form. Over the past twenty-five years a highly sophisticated technology has developed in this area. From the relatively simplistic growth of ammonium and potassium dihydrogen phosphates (ADP and KDP) from saturated solutions for transducer elements, a level has been obtained at which pure metals (Cu, Pb, Al, Ag, Fe, etc.), a semi-metals (Si, Ge, As, etc.), and compounds (GaAs, InAs, InSb, InP, etc.) are available and even essential in large single crystal form to the electronics industries. Synthetic gems (rubies, spinels, sapphires, emeralds, and zircons) are single crystals of aluminum, beryllium, and zirconium silicates or oxides with controlled impurity levels of transition elements.

Growth of such single crystals can follow several techniques, with thermodynamic constraints dictating the technique for any particular material: crystallization by cooling a supersaturated solution of a compound in a high-temperature flux; crystallization by dropping powder through an intense flame onto a seed pedestal, known as the Verneuil technique (see Fig. 6); crystallization by pulling a "seed" crystal from the surface of a liquid melt, known as the Czochralski method (see Fig. 7); crystallization by lowering a melt through a small, controlled thermal gradient, known as the Stockbarger technique (see Fig. 8); crystallization by zone-melting, known as the Pfann method (see Fig. 9); and crystallization by the vapor-phase approach (see Fig. 10). All of these procedures, however, require three essential ingredients: (1) A good "seed" crystal from which spiral and sometimes oriented growth can occur and develop; (2) highly precise operational conditions—movement of fractions of a millimeter, or temperature variations of 0.5°C per hour; and (3), as previously indicated, materials of a specific impurity level. Given these conditions, single crystals can be grown in large quantities—ranging from the multimillion carat operations of Linde (United States) and Djévaheeridjian (Switzerland), using the Verneuil technique, to the multikilo manufacture of single crystal silicon by Texas Instruments Incorporated (United States), employing the Czochralski and zone melt methods, and including a 27-kilogram single crystal of dislocation-free silicon by the Kayex Corporation (United States) grown by a modified Czochralski approach.

See also Semiconductor.

Dislocation in Crystalline Solids. This type of imperfection in a crystalline solid is generated as follows: A closed curve is drawn within the solid, and a cut made along any simple surface which has this curve as boundary. The material on one side of this surface is displaced by a fixed amount called the Burgers vector relative to the other side. Any gap or overlap is made good by the addition or removal of material, and the two sides are then rejoined, leaving the strain displacement intact at the moment of rewelding, but afterwards allowing the medium to come to internal equilibrium. If the Burgers vector represents a translation vector of the lattice, the weld is invisible, and the dislocation is characterized only by the original curve, or dislocation line and by the Burgers vector.